

# 2SK2835

Chopper Regulator, DC-DC Converter and Motor Drive Applications

- Low drain-source ON resistance :  $R_{DS(ON)} = 0.56 \Omega$  (typ.)
- High forward transfer admittance :  $|Y_{fs}| = 4.5 S$  (typ.)
- Low leakage current :  $I_{DSS} = 100 \mu A$  (max) ( $V_{DS} = 200 V$ )
- Enhancement mode :  $V_{th} = 1.5 \sim 3.5 V$  ( $V_{DS} = 10 V, I_D = 1 mA$ )

## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	200	V
Drain-gate voltage ( $R_{GS} = 20 k\Omega$ )		$V_{DGR}$	200	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	5	A
	Pulse (Note 1)	$I_{DP}$	20	
Drain power dissipation		$P_D$	1.3	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	65	mJ
Avalanche current		$I_{AR}$	5	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	0.13	mJ
Channel temperature		$T_{ch}$	150	$^\circ C$
Storage temperature range		$T_{stg}$	-55~150	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

## Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	96.1	$^\circ C / W$

Note 1: Ensure that the channel temperature does not exceed  $150^\circ C$ .

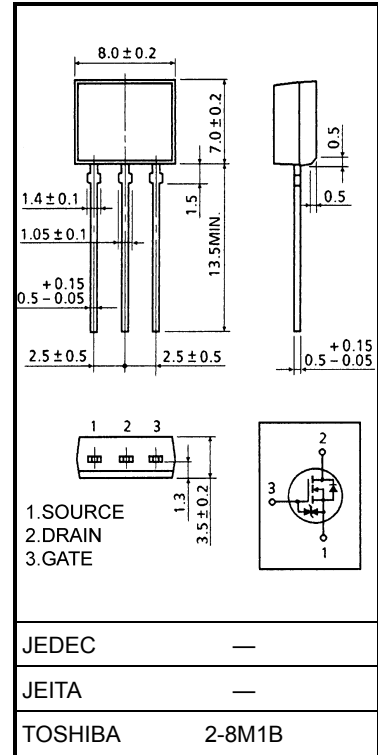
Note 2:  $V_{DD} = 50 V, T_{ch} = 25^\circ C$  (initial),  $L = 4.2 mH, R_G = 25 \Omega, I_{AR} = 5 A$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

Unit: mm



Weight: 0.54 g (typ.)

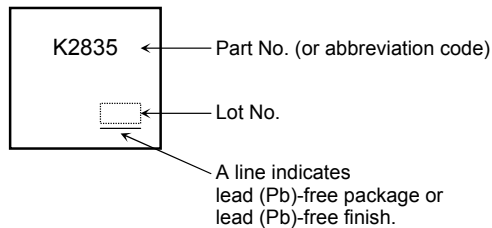
## Electrical Characteristics (Ta = 25°C)

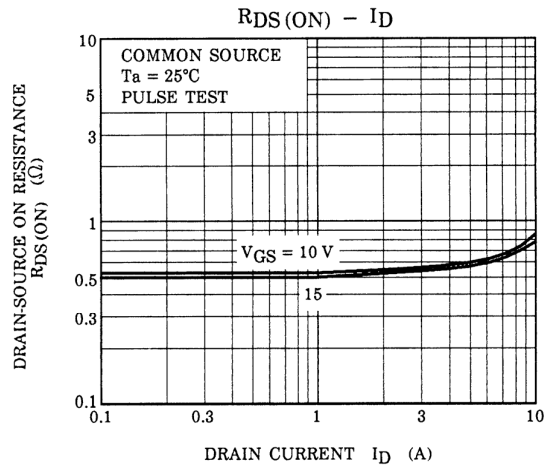
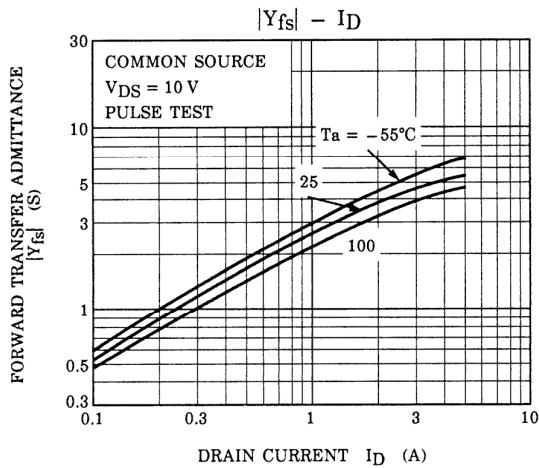
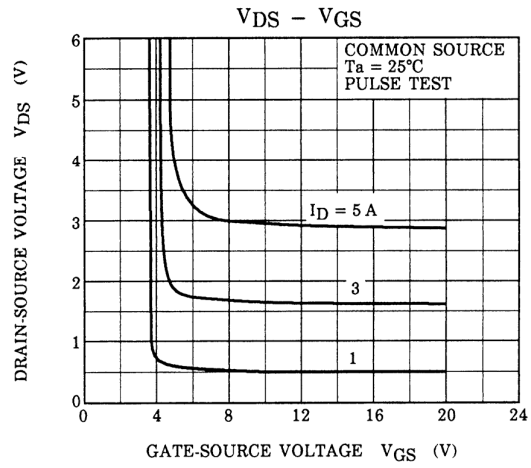
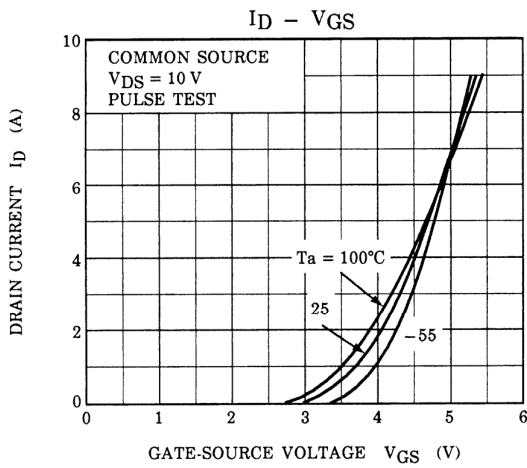
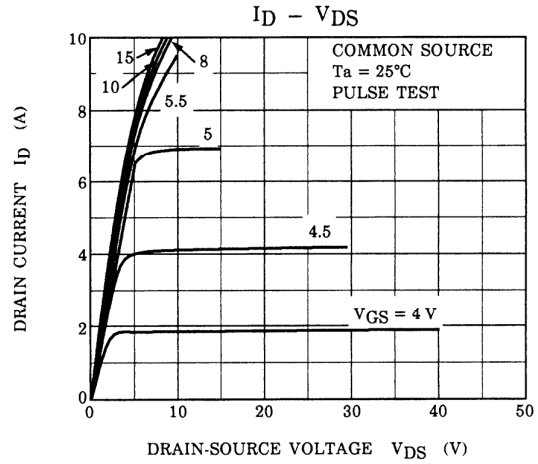
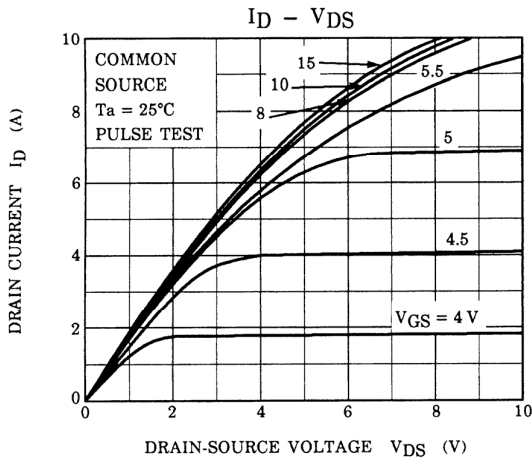
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$	
Drain cut-off current	$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	—	—	100	$\mu\text{A}$	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}$	200	—	—	V	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$	1.5	—	3.5	V	
Drain-source ON resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$	—	0.56	0.8	$\Omega$	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 10\text{ V}, I_D = 2.5\text{ A}$	2.0	4.5	—	S	
Input capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	440	—	pF	
Reverse transfer capacitance	$C_{rss}$		—	35	—		
Output capacitance	$C_{oss}$		—	120	—		
Switching time	Rise time	$t_r$		—	15	—	ns
	Turn-on time	$t_{on}$		—	20	—	
	Fall time	$t_f$		—	15	—	
	Turn-off time	$t_{off}$		—	60	—	
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	—	10	—	nC	
Gate-source charge	$Q_{gs}$		—	6	—		
Gate-drain ("miller") Charge	$Q_{gd}$		—	4	—		

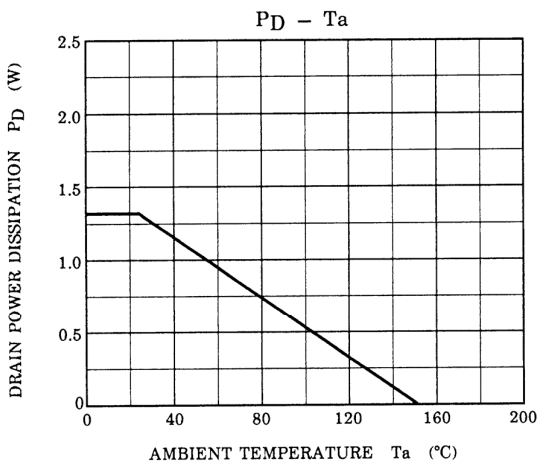
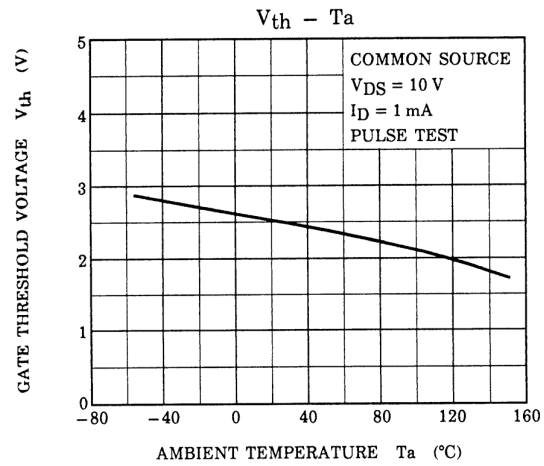
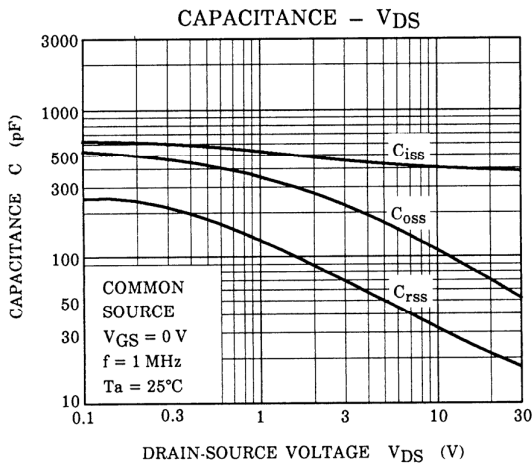
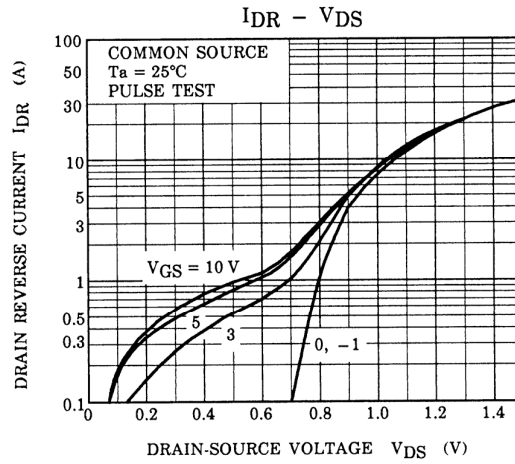
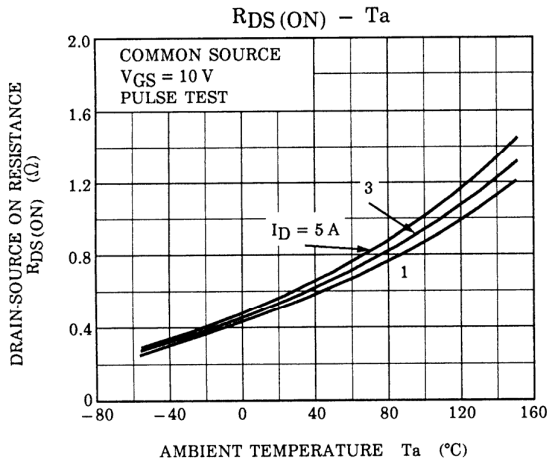
## Source-Drain Ratings and Characteristics (Ta = 25°C)

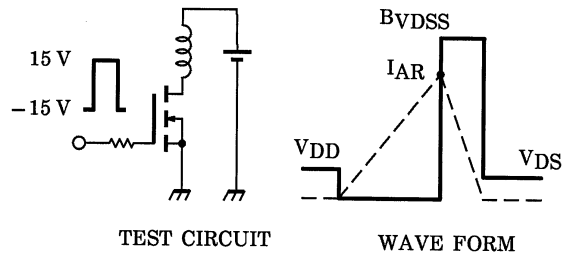
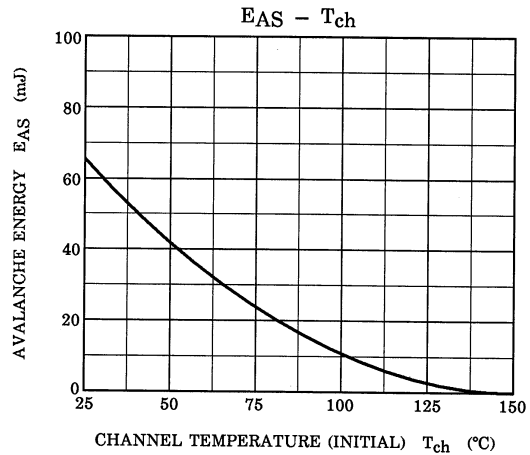
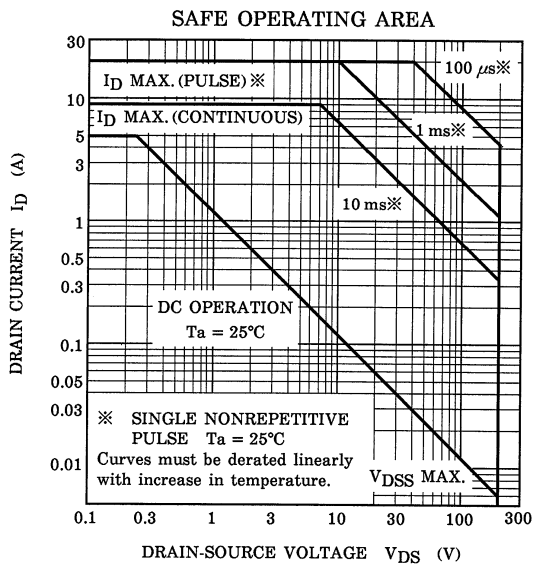
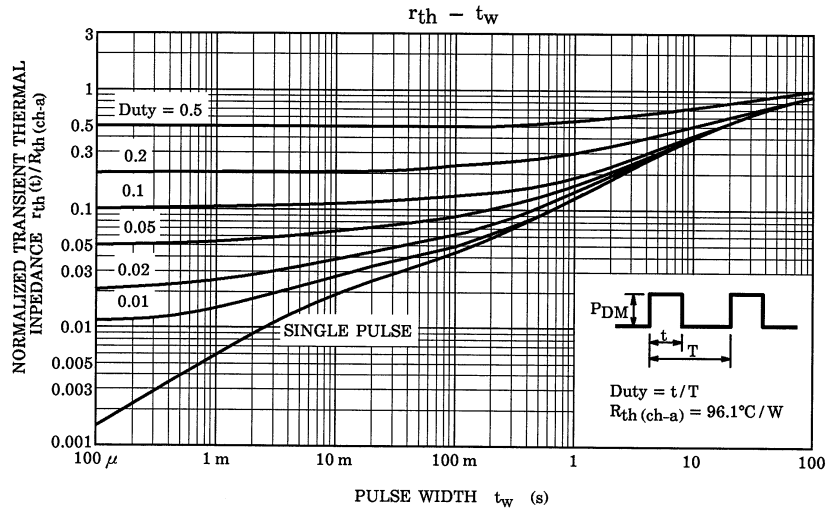
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	5	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	20	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}$	—	—	-2.0	V
Reverse recovery time	$t_{rr}$	$I_{DR} = 5\text{ A}, V_{GS} = 0\text{ V}, dI_{DR} / dt = 100\text{ A} / \mu\text{s}$	—	150	—	ns
Reverse recovery charge	$Q_{rr}$		—	0.45	—	$\mu\text{C}$

## Marking









$R_G = 25 \Omega$   
 $V_{DD} = 25 V, L = 4.2 mH$

$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$

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